

Supporting Information

Tuning of the electronic, photocatalytic and optical properties of Janus XWAZ₂ (X=S, Se, Te; A = Si, Ge; Z=N, P, As) monolayers *via* strain and external electric field

Zhen Gao^a, Xin He^a, YaoHe^{a,*}, and Kai Xiong^b

^a*Department of Physics, Yunnan University, Kunming 650091, People's Republic of China.*

^b*Materials Genome Institute, School of Materials and Energy, Yunnan University, Kunming 650091, P. R. China.*

*E-mail:
yhe@ynu.edu.cn

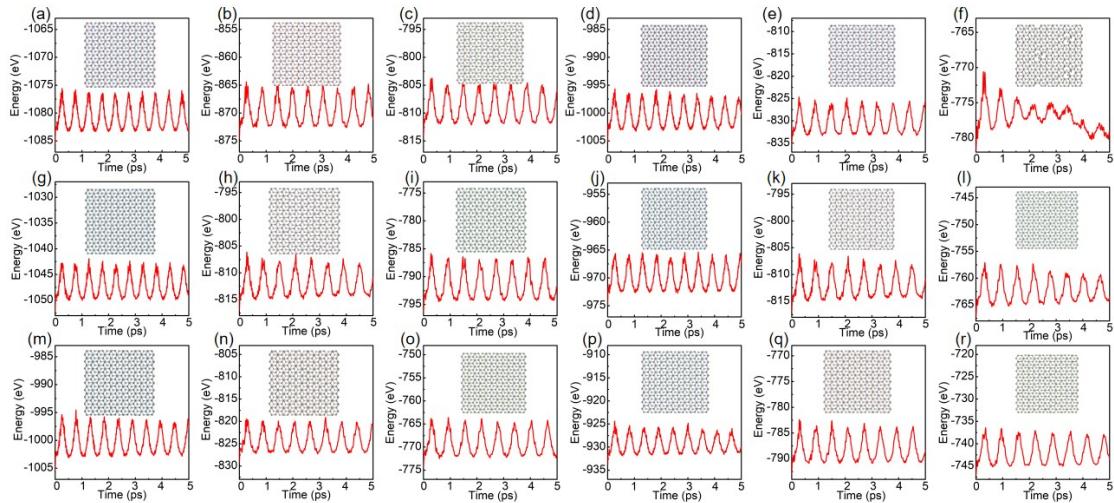


Fig S1 Variation of the energy as a function of time for the Janus (a)SWSiN₂, (b)SWSiP₂, (c)SWSiAs₂, (d)SWGeN₂, (e)SWGEP₂, (f)SWGeAs₂, (g)SeWSiN₂, (h)SeWSiP₂, (i)SeWSiAs₂, (j)SeWGeN₂, (k)SeWGeP₂, (l)SeWGeAs₂, (m)TeWSiN₂, (n)TeWSiP₂, (o)TeWSiAs₂, (p)TeWGeN₂, (q)TeMoGeP₂ and (r)TeWGeAs₂ monolayer monolayers at 300K. The insets are the top view of the structure at the end of the AIMD simulation.

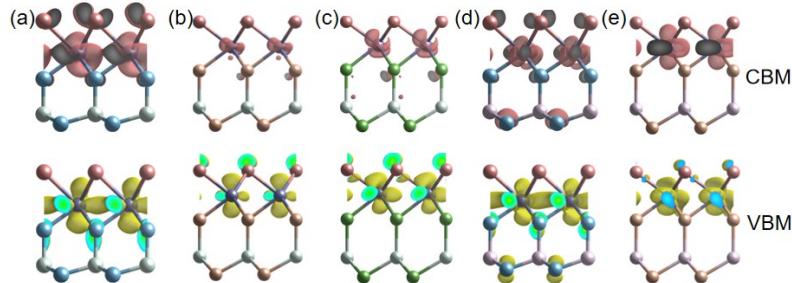


Fig S2 The charge density of the CBM and VBM of (a)SWSiN₂, (b)SWSiP₂, (c)SWSiAs₂, (d)SWGeN₂, and (e)SWGEP₂ monolayers. The CBM and VBM are marked in red and yellow, respectively. The isosurface values of SWAZ₂ monolayers are taken as 0.015 eÅ⁻³.

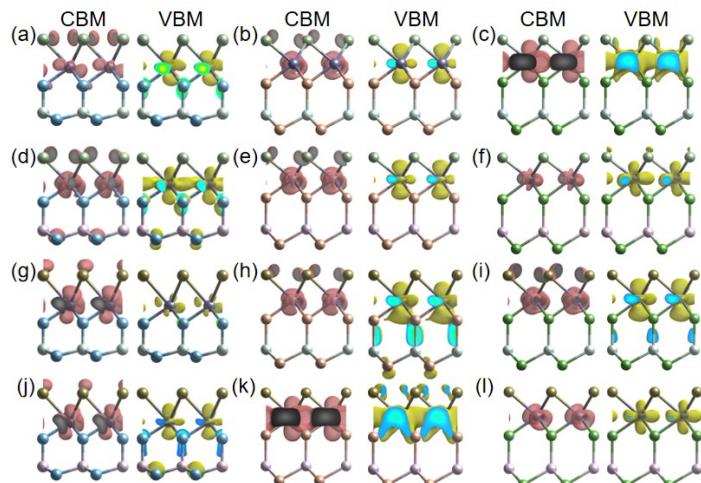


Fig S3 The charge density of the CBM and VBM of (a)SeWSiN₂, (b)SeWSiP₂, (c)SeWSiAs₂, (d)SeWGeN₂, (e)SeWGeP₂, (f)SeWGeAs₂, (g)TeWSiN₂, (h)TeWSiP₂, (i)TeWSiAs₂, (j)TeWGeN₂, (k)TeMoGeP₂ and (l)TeWGeAs₂ monolayers. The CBM and VBM are marked in red and yellow, respectively. The isosurface values of SWAZ₂ monolayers are taken as 0.015 eÅ⁻³.

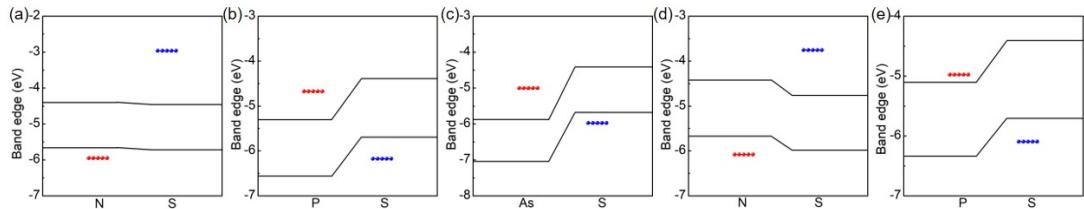


Fig S4 Band alignments with regard to the vacuum level of pristine (a) SWSiN₂, (b) SWSiP₂, (c) SWSiAs₂, (d) SWGeN₂ and (e) SWGeP₂ under the HSE06 functional.

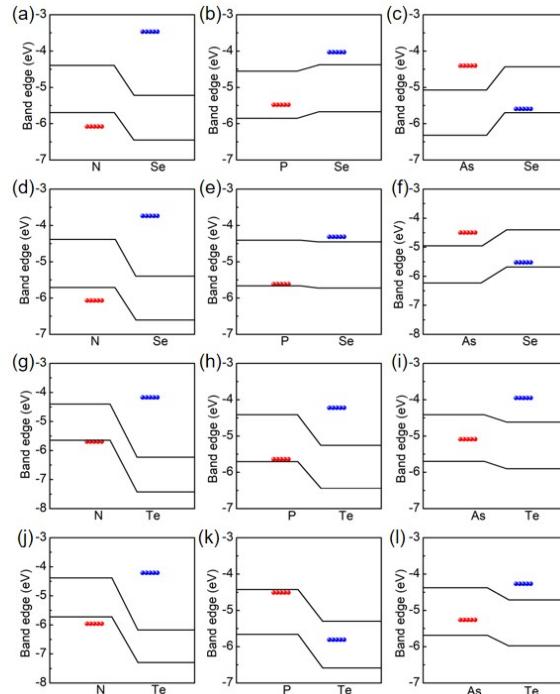


Fig S5 Band alignments with regard to the vacuum level of pristine (a)SeWSiN₂, (b)SeWSiP₂, (c)SeWSiAs₂, (d)SeWGeN₂, (e)SeWGeP₂, (f)SeWGeAs₂, (g)TeWSiN₂, (h)TeWSiP₂, (i)TeWSiAs₂, (j)TeWGeN₂, (k)TeMoGeP₂ and (l)TeWGeAs₂ monolayers under the HSE06 functional.

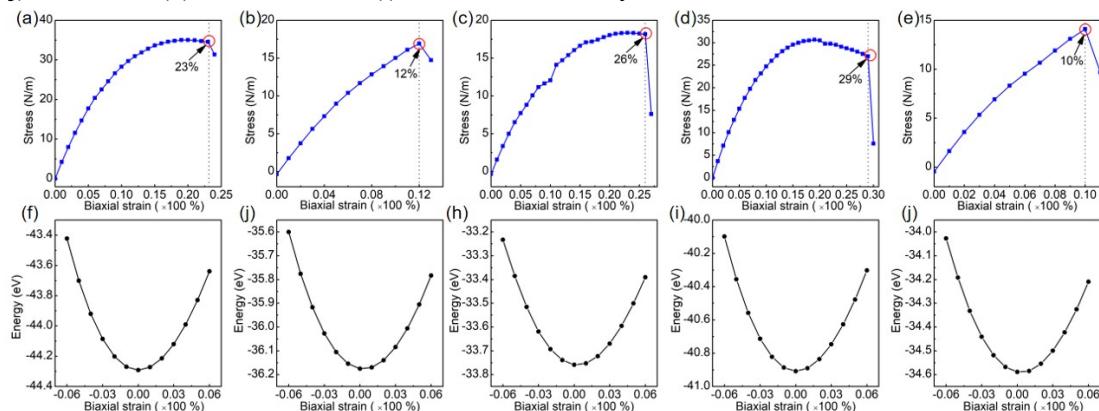


Fig S6 (a-e) Strain-stress curve and (f-j) energy-strain curves for 2D Janus SWSiN₂, SWSiP₂, SWSiAs₂, SWGeN₂ and SWGeP₂ monolayers.

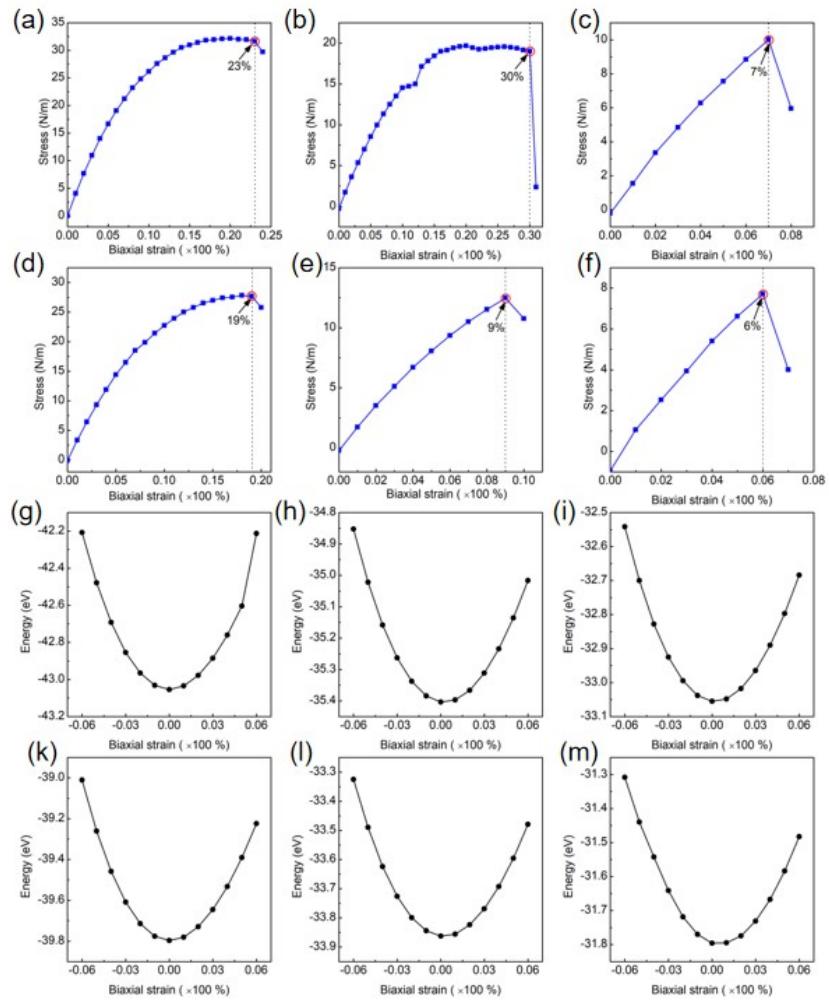


Fig S7 (a-f) Strain-stress curve and (g-m) energy-strain curves for 2D Janus SeWSiN₂, SeWSiP₂, SeWSiAs₂, SeWGeN₂, SeWGeP₂, and SeWGeAs₂ monolayers.

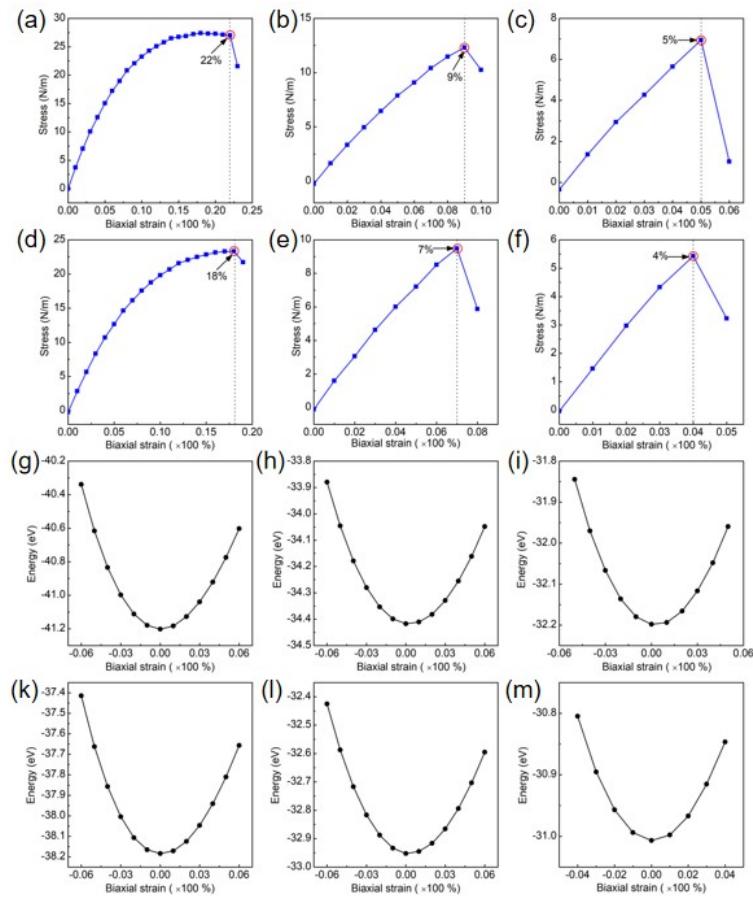


Fig S8 (a-f) Strain-stress curve and (g-m) energy-strain curves for 2D Janus TeWSiN₂, TeWSiP₂, TeWSiAs₂, TeWGeN₂, TeWGeP₂, and TeWGeAs₂ monolayers.

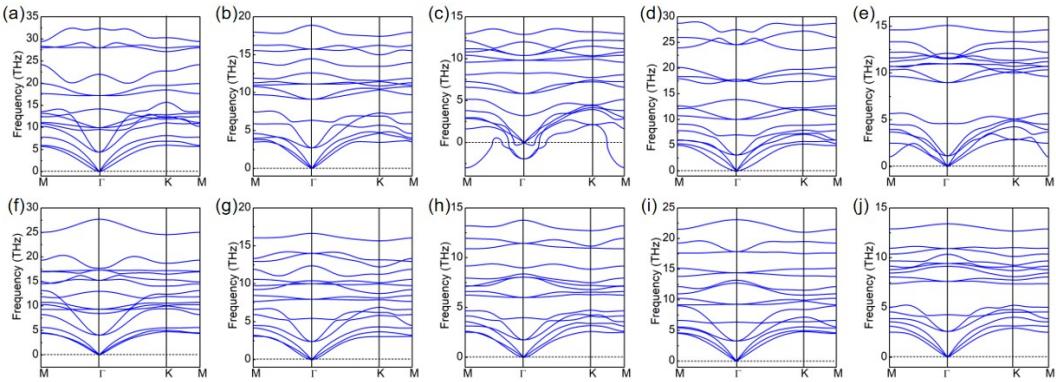


Fig S9 Phonon spectrum of SWSiN₂, SWSiP₂, SWSiAs₂, SWGeN₂, and SWGeP₂ monolayers under strain of (a-e) -6% and (f-j) +6%, respectively.

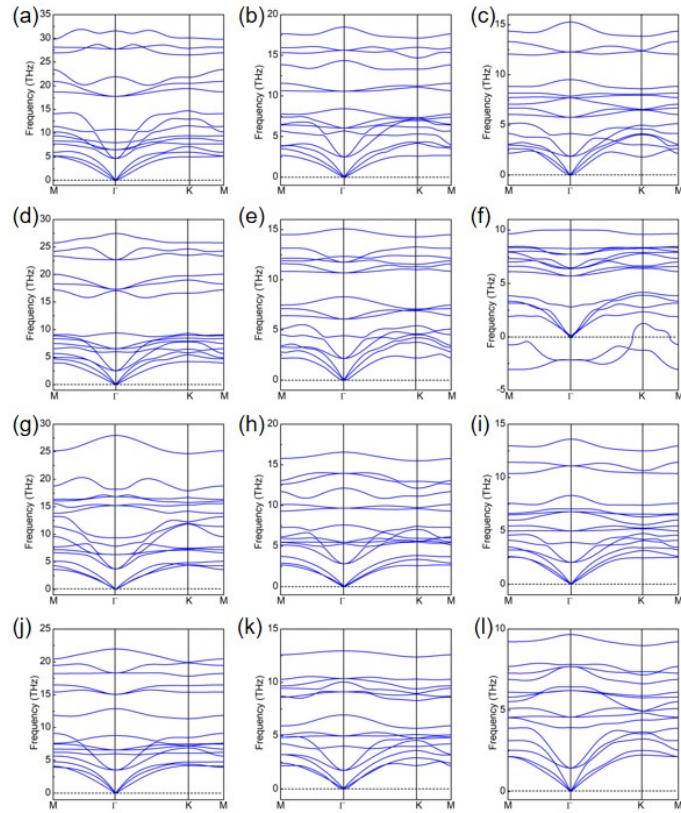


Fig S10 Phonon spectrum of SeWSiN₂, SeWSiP₂, SeWSiAs₂, SeWGeN₂, SeWGeP₂ and SeWGeAs₂ monolayers under strain of (a-f) -6% and (g-l) +6%, respectively.

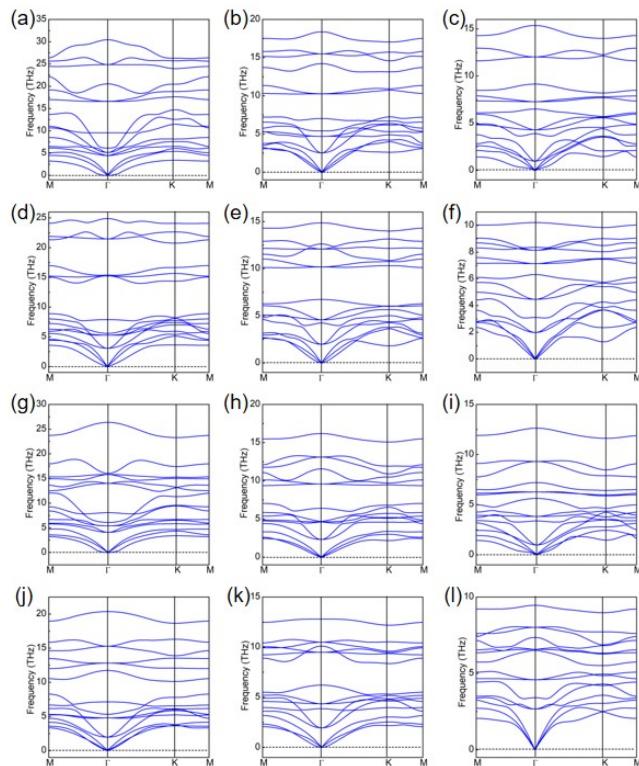


Fig S11 Phonon spectrum of TeWSiN₂, TeWSiP₂, TeWGeN₂, and TeWGeP₂ monolayers under strain of (a, b, d, e) -6% and (g, h, j, k) +6%, respectively. TeWSiAs₂ monolayer under strain of (c) -5% and (i) +5%. TeWGeAs₂ monolayer under strain of (f) -4% and (l) +5%.

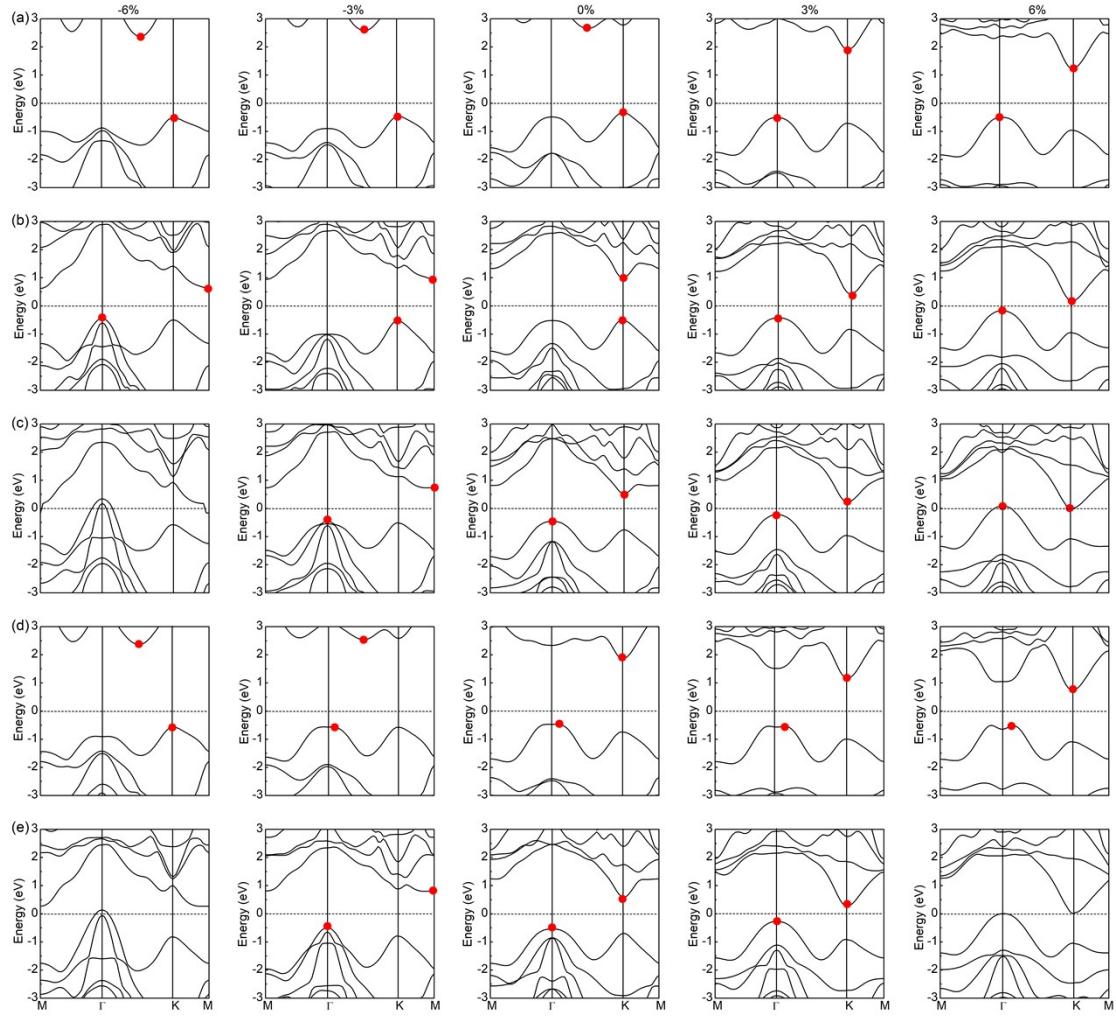


Fig S12 Band structure under biaxial strain of 2D Janus (a) SWSiN₂, (b) SWSiP₂, (c) SWSiAs₂, (d) SWGeN₂ and (e) SWGeP₂ monolayers.

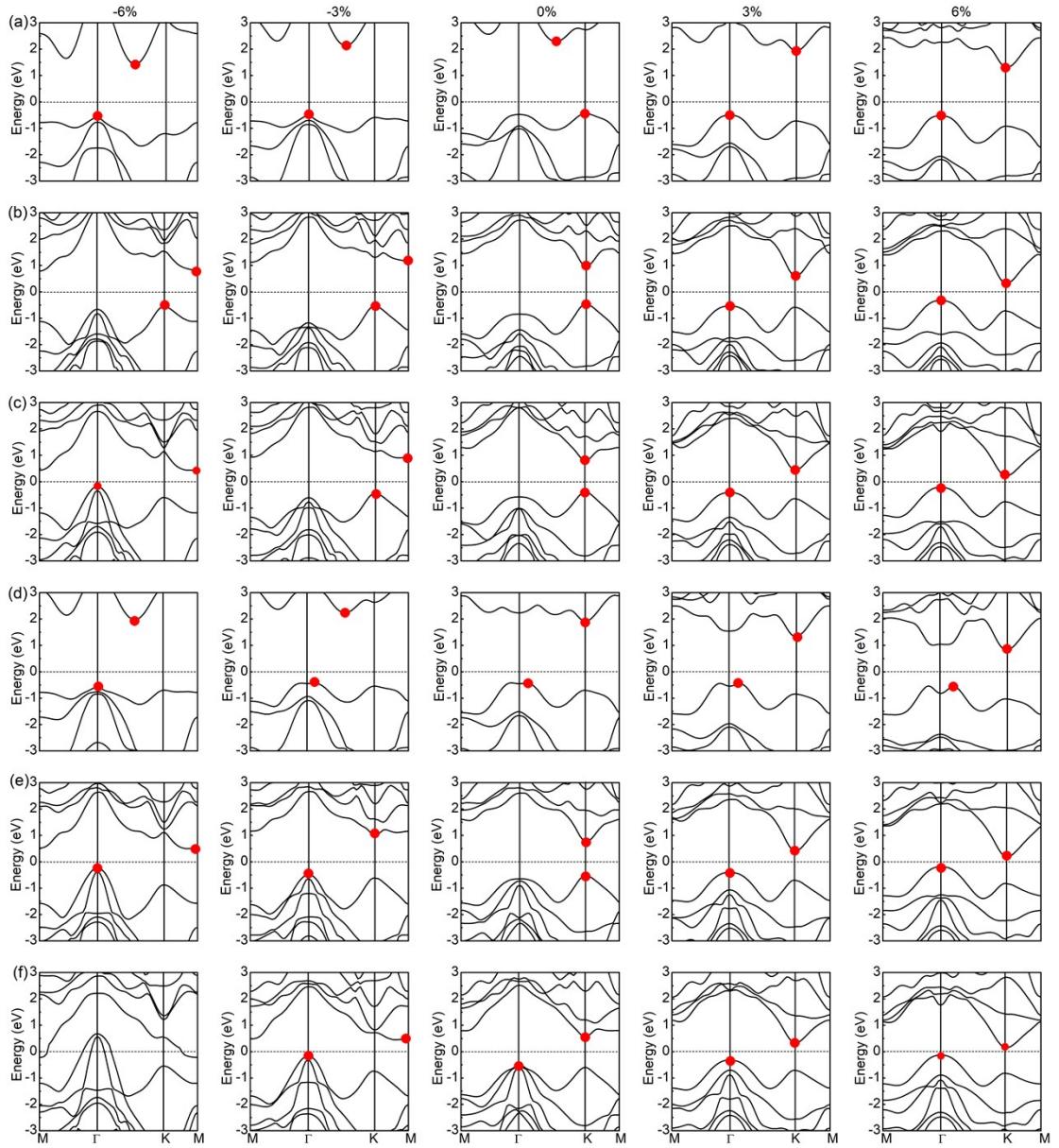


Fig S13 Band structure under biaxial strain of 2D Janus (a) SeWSiN₂, (b) SeWSiP₂, (c) SeWSiAs₂, (d) SeWGeN₂, (e) SeWGeP₂ and (f) SeWGeAs₂ monolayers.

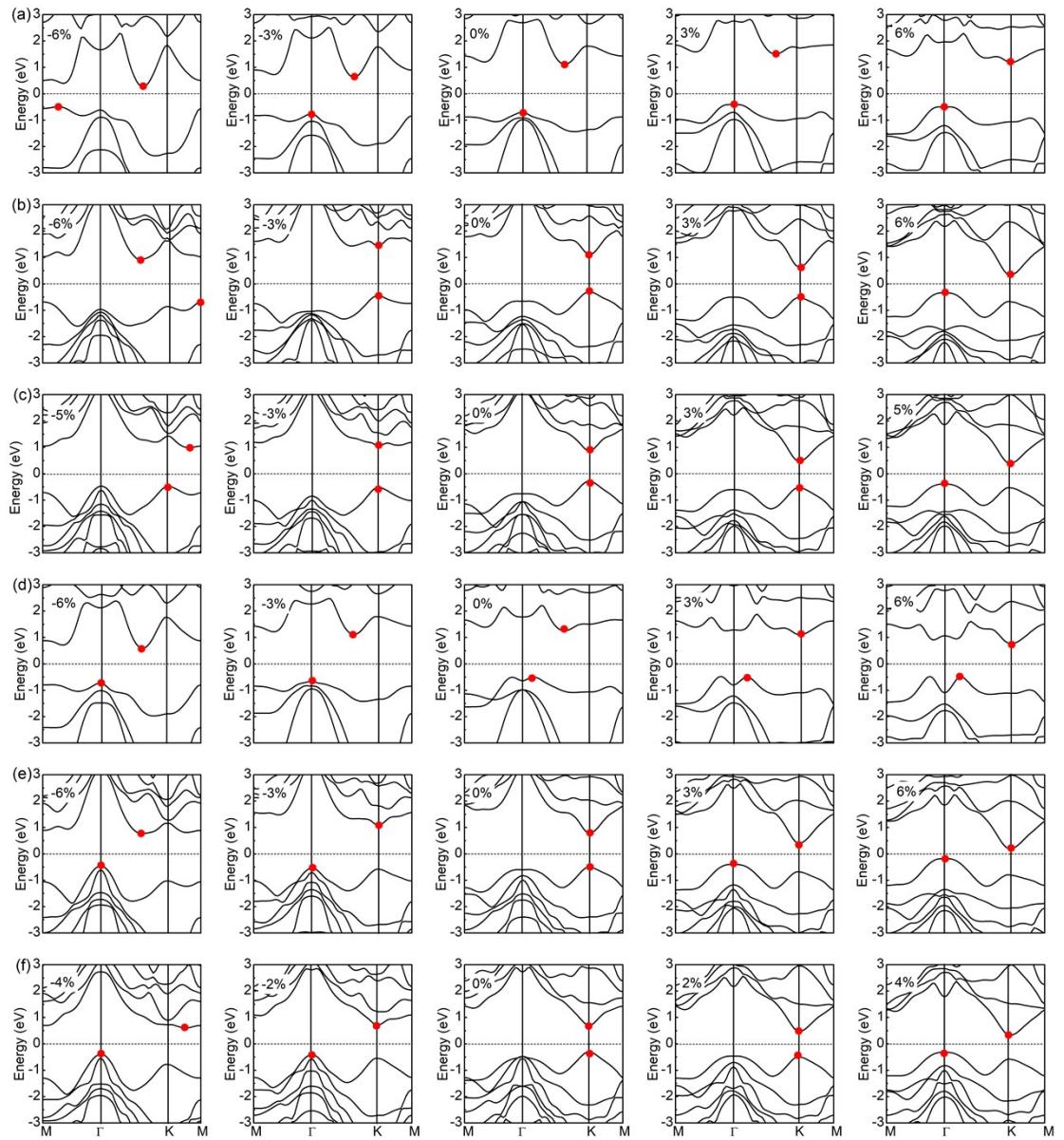


Fig S14 Band structure under biaxial strain of 2D Janus (a) TeWSiN₂, (b) TeWSiP₂, (c) TeWSiAs₂, (d) TeWGeN₂, (e) TeWGeP₂ and (f) TeWGeAs₂ monolayers.

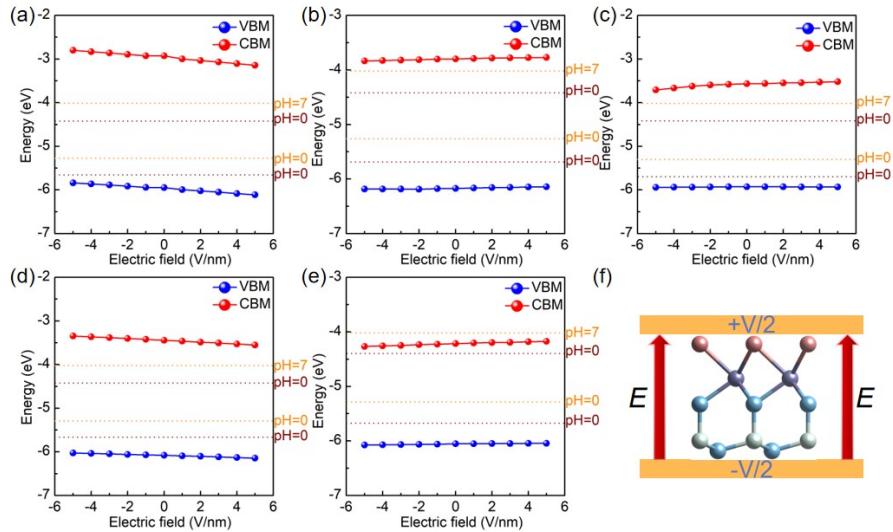


Fig S15 Band alignments of Janus (a) SWSiN₂, (b) SWSiP₂, (c) SWSiAs₂, (d) SWGeN₂, and (e) SWGeP₂ under external electric field. (f) The top view of Janus XWAZ₂(X=S, Se, Te; A=Si, Ge; Z=N, P, As) under external electric field.

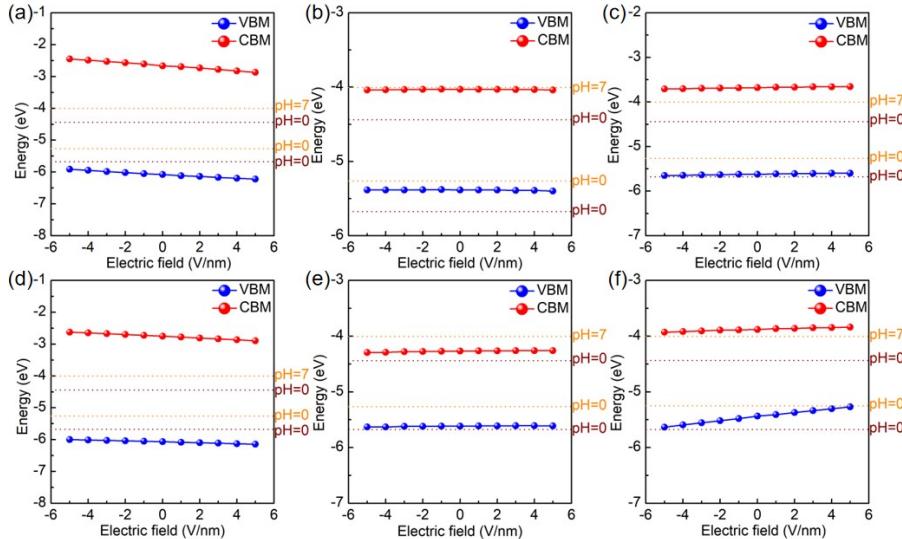


Fig S16 Band alignments of Janus (a) SeWSiN₂, (b) SeWSiP₂, (c) SeWSiAs₂, (d) SeWGeN₂, (e) SeWGeP₂, and (f) SeWGeAs₂ under external electric field.

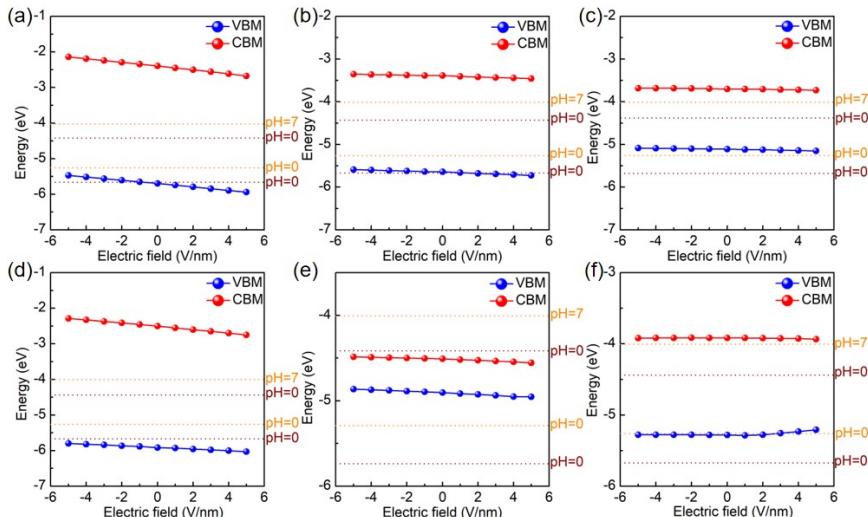


Fig S17 Band alignments of Janus (a) TeWSiN₂, (b) TeWSiP₂, (c) TeWSiAs₂, (d) TeWGeN₂, (e) TeWGeP₂, and (f) TeWGeAs₂ under external electric field.

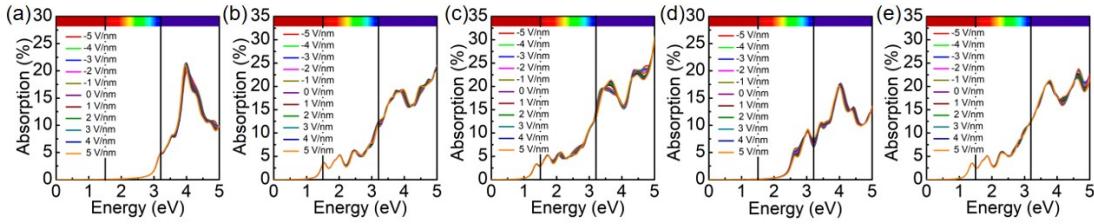


Fig S18 The light absorption of Janus (a) SWSiN₂, (b) SWSiP₂, (c) SWSiAs₂, (d) SWGeN₂, and (e) SWGeP₂ with external electric field.

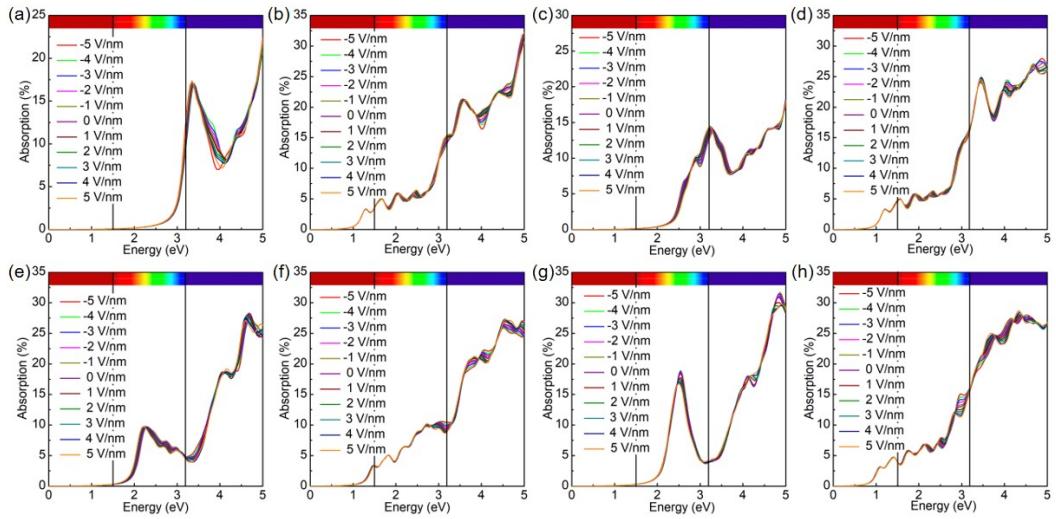


Fig S19 The light absorption of Janus (a) SeWSiN₂, (b) SeWSiAs₂, (c) SeWGeN₂, (d) SWGeAs₂, (e) TeWSiN₂, (f) TeWSiP₂, (g) TeWGeN₂, and (h) TeWGeAs₂ with external electric field.